

STN

HCAPLUS, USPATALL, DATED, INSPR

9/17/00

=> d 18 1-8 abs, bib

L8 ANSWER 1 OF 8 HCAPLUS COPYRIGHT 2003 ACS on STN

AB Polycryst. Si ingots for use in photoconversion technol. are obtained by melting Si in a SiO₂ crucible, allowing the melt to cool and to crystallize, rotating the crucible for 180.degree. around a horizontal axis, and heating the crucible bottom to melt the film of Si adhering to the **crucible** and to **detach** the ingot by gravity.

AN 1982:184235 HCAPLUS

DN 96:184235

TI Method and apparatus for preparing a **polycrystalline silicon** ingot

IN Guenel, Claude; Fally, Jacques

PA Compagnie Generale d'Electricite S. A., Fr.

SO Fr. Demande, 15 pp.

CODEN: FRXXBL

DT Patent

LA French

FAN. CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	FR 2477047	A1	19810904	FR 1980-4543	19800229
PRAI	FR 1980-4543		19800229		

L8 ANSWER 2 OF 8 USPATFULL on STN

AB A crucible 1 made of a C/C composite material for use in single crystal pulling, the crucible 1 having a lateral cylindrical portion 11 and a bottom portion 12 integrally formed as multiple layers wound by a filament winding method, in which the first layer 2 as the innermost crucible layer, among the multiple layers, is wound such that carbon fibers form tracks passing the polar point O at the bottom 12, the second layer 3 wound on the outer surface of the first layer 2 is wound along tracks to form a first outer circular bottom 8 that extends outwardly from about a middle part of a raised portion 6 where the carbon fibers of the first layer 2 are localized to the polar point O, and the third layer 4 and the succeeding layers wound on the outer surface of the second layer 3 are wound respectively along tracks to form outer circular bottoms that extend stepwise outwardly from about the middle parts of the outer surfaces of layers situated inside the respective layers, and the top for the raised portion of the first layer and the top for each of the outer circular bottoms at the bottom of the carbon fibers wound around as the multiple layers are at an substantially identical height, detachment and deformation of carbon fibers during use being suppressed by reducing the machining for the bottom of the crucible after molding.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2002:327408 USPATFULL

TI Crucible made of carbon fiber-reinforced carbon composite material for single crystal pulling apparatus

IN Yamaji, Masatoshi, Mitoyo-gun, JAPAN

Nishi, Hisanori, Mitoyo-gun, JAPAN

Tomita, Yuji, Mitoyo-gun, JAPAN

Bito, Shingo, Mitoyo-gun, JAPAN

Miyatani, Toshiyuki, Mitoyo-gun, JAPAN

PA Toyo Tanso Co., Ltd., Osaka-shi, JAPAN (non-U.S. corporation)

PI US 2002185061 A1 20021212

AI US 2002-136531 A1 20020502 (10)

PRAI JP 2001-134762 20010502

DT Utility

FS APPLICATION

LREP OBLON SPIVAK MCCLELLAND MAIER & NEUSTADT PC, FOURTH FLOOR, 1755

JEFFERSON DAVIS HIGHWAY, ARLINGTON, VA, 22202

CLMN Number of Claims: 3

ECL Exemplary Claim: 1

DRWN 7 Drawing Page(s)

LN.CNT 678

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L8 ANSWER 3 OF 8 USPATFULL on STN

AB A crucible used in the growth of **polycrystal silicon** by a cast method comprises a crucible body for, when solid material silicon is melted, containing the melted material silicon, and a material holder provided on the crucible body, for holding further material silicon on the material silicon loaded into the crucible body.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2002:162309 USPATFULL

TI Crucible and growth method for **polycrystal silicon** using same

IN Katoh, Nobuyuki, Yoshino-gun, JAPAN

PI US 2002083886 A1 20020704

AI US 2001-994022 A1 20011127 (9)

PRAI JP 2000-367779 20001201

DT Utility

FS APPLICATION

LREP NIXON & VANDERHYE P.C., 8th Floor, 1100 Noth Glebe Road, Arlington, VA, 22201-4714

CLMN Number of Claims: 9

ECL Exemplary Claim: 1

DRWN 4 Drawing Page(s)

LN.CNT 350

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L8 ANSWER 4 OF 8 USPATFULL on STN

AB A (111) cubic silicon carbide single-crystal layer is formed on a (111) silicon wafer, and then the silicon wafer is removed. Thus prepared (111) cubic silicon carbide single-crystal layer is disposed in a graphite crucible to function as a seed crystal. Silicon carbide source material powder is also held in the graphite crucible and sublimated in an atmosphere including inert gas, while controlling a temperature of the (111) cubic silicon carbide single-crystal layer to be lower than a temperature of the silicon carbide source material powder. As a result, a (0001) α -type silicon carbide single-crystal layer can be formed on the (111) cubic silicon carbide single-crystal layer with a large diameter and high quality at low cost.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2000:113308 USPATFULL

TI Method of producing single-crystal silicon carbide

IN Kito, Yasuo, Okazaki, Japan

Kotanshi, Youichi, Okazaki, Japan

Onda, Shoichi, Toyokawa, Japan

Hanazawa, Tatuuyuki, Okazaki, Japan

Kitaoka, Eiji, Anjo, Japan

PA Denso Corporation, Kariya, Japan (non-U.S. corporation)

PI US 6110279 20000829

AI US 1998-49979 19980330 (9)

RLI Continuation-in-part of Ser. No. US 1997-826147, filed on 27 Mar 1997, now abandoned

PRAI JP 1996-75775 19960329

JP 1997-129875 19970520

JP 1997-163087 19970619

DT Utility

FS Granted

EXNAM Primary Examiner: Hiteshew, Felisa
LREP Pillsbury, Madison & Sutro, LLP
CLMN Number of Claims: 48
ECL Exemplary Claim: 1
DRWN 34 Drawing Figure(s); 11 Drawing Page(s)
LN.CNT 1386
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L8 ANSWER 5 OF 8 USPATFULL on STN

AB In a method of producing single crystals on a seed crystal, the seed crystal is covered by a protection layer except for a surface on which the single crystals are to be formed. The protection layer is made of material such as carbon or the like, which is stable in a step of forming the single crystals. As a result, a temperature gradient and mass transfer in the seed crystal can be prevented, whereby quality of the single crystals formed on the seed crystal can be improved.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 1999:102280 USPATFULL
TI Method of producing single crystals and a seed crystal used in the method
IN Kitou, Yasuo, Okazaki, Japan
Sugiyama, Naohiro, Nagoya, Japan
Okamoto, Atsuto, Nagoya, Japan
Tani, Toshihiko, Nagoya, Japan
Kamiya, Nobuo, Nisshin, Japan
PA Denso Corporation, Kariya, Japan (non-U.S. corporation)
PI US 5944890 19990831
AI US 1997-829449 19970328 (8)
PRAI JP 1996-75776 19960329
JP 1996-103581 19960329
DT Utility
FS Granted
EXNAM Primary Examiner: Hiteshew, Felisa
LREP Pillsbury Madison & Sutro LLP
CLMN Number of Claims: 21
ECL Exemplary Claim: 1
DRWN 17 Drawing Figure(s); 6 Drawing Page(s)
LN.CNT 915
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L8 ANSWER 6 OF 8 USPATFULL on STN

AB A silicon melting crucible having a double structure, in which a quartz crucible is inserted inside of a carbon crucible, is provided with devices for preventing deformation, such as turning-down, buckling and bending at an upper portion of the quartz crucible, or invasion of an SiO gas into a space between the quartz crucible and the carbon crucible during pulling up of a silicon single crystal. According to one form of the invention an upper portion of the quartz crucible has a frusto-conical inclined portion with an angle of inclination desirably of from 5.degree. to 40.degree.. According to another form of the invention a carbon ring having a cross section of either L-shape or U-shape is applied to the upper portion of the quartz crucible and the carbon crucible.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 1999:75165 USPATFULL
TI Silicon melting crucible
IN Takemura, Kaoru, Amagasaki, Japan
PA Sumitomo Sitix Corporation, Amagasaki, Japan (non-U.S. corporation)
PI US 5919306 19990706
AI US 1997-963064 19971103 (8)
DT Utility

LREP Morris, Birgit E., Swope, R. Hain
CLMN Number of Claims: 11
ECL Exemplary Claim: 1
DRWN 3 Drawing Figure(s); 2 Drawing Page(s)
LN.CNT 333
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

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(FILE 'HCAPLUS, USPATFULL, USPAT2, JAPIO, INSPEC' ENTERED AT 13:01:02 ON
17 SEP 2003)

DELETE HIS

L1 166 S (CRUCIBLE) (8A) (DETACH?)
L2 62600 S (POLYCRYSTAL?) (8A) (SI OR SILICON)
L3 61255 S (CAST?) (8A) (METHOD?)
L4 1756 S (CRUCIBLE#) (8A) (SILICA)
L5 1921034 S (CARBON)
L6 1 S L1 AND L2 AND L3 AND L4 AND L5
L7 1 S L1 AND L2 AND L3
L8 8 S L1 AND L2

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=> d his

(FILE 'HCAPLUS, USPATFULL, USPAT2, JAPIO, INSPEC' ENTERED AT 13:01:02 ON
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L4 1756 S (CRUCIBLE#) (8A) (SILICA)
L5 1921034 S (CARBON)

=> s l1 and l2 and l3 and l4 and l5

L6 1 L1 AND L2 AND L3 AND L4 AND L5

=> d l6 abs,bib

L6 ANSWER 1 OF 1 USPATFULL on STN

AB A crucible used in the growth of **polycrystal silicon**
by a **cast method** comprises a crucible body for, when
solid material silicon is melted, containing the melted material
silicon, and a material holder provided on the crucible body, for
holding further material silicon on the material silicon loaded into the
crucible body.

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AN 2002:162309 USPATFULL

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22201-4714

CLMN Number of Claims: 9

ECL Exemplary Claim: 1

DRWN 4 Drawing Page(s)

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